DIGIPREDICT

DESIGN AND SIMULATION OF A CNT STRAIN SENSOR WITH LOW MECHANICAL CROSS-SENSITIVITY

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a)

Motivation

- Use of individual, suspended carbon nanotubes in a transistor-like structure as strain sensor
- Measuring skin strain to monitor respiration activity
 - High sensitivity and high gauge factor
 - Ultra-miniaturized size potentially reducing motion artefacts
- Requirements for the mechanical design
 - Allows only one directional strain detection
 - Allows dry transfer of ultra-clean CNTs
 - Enables appropriate handling

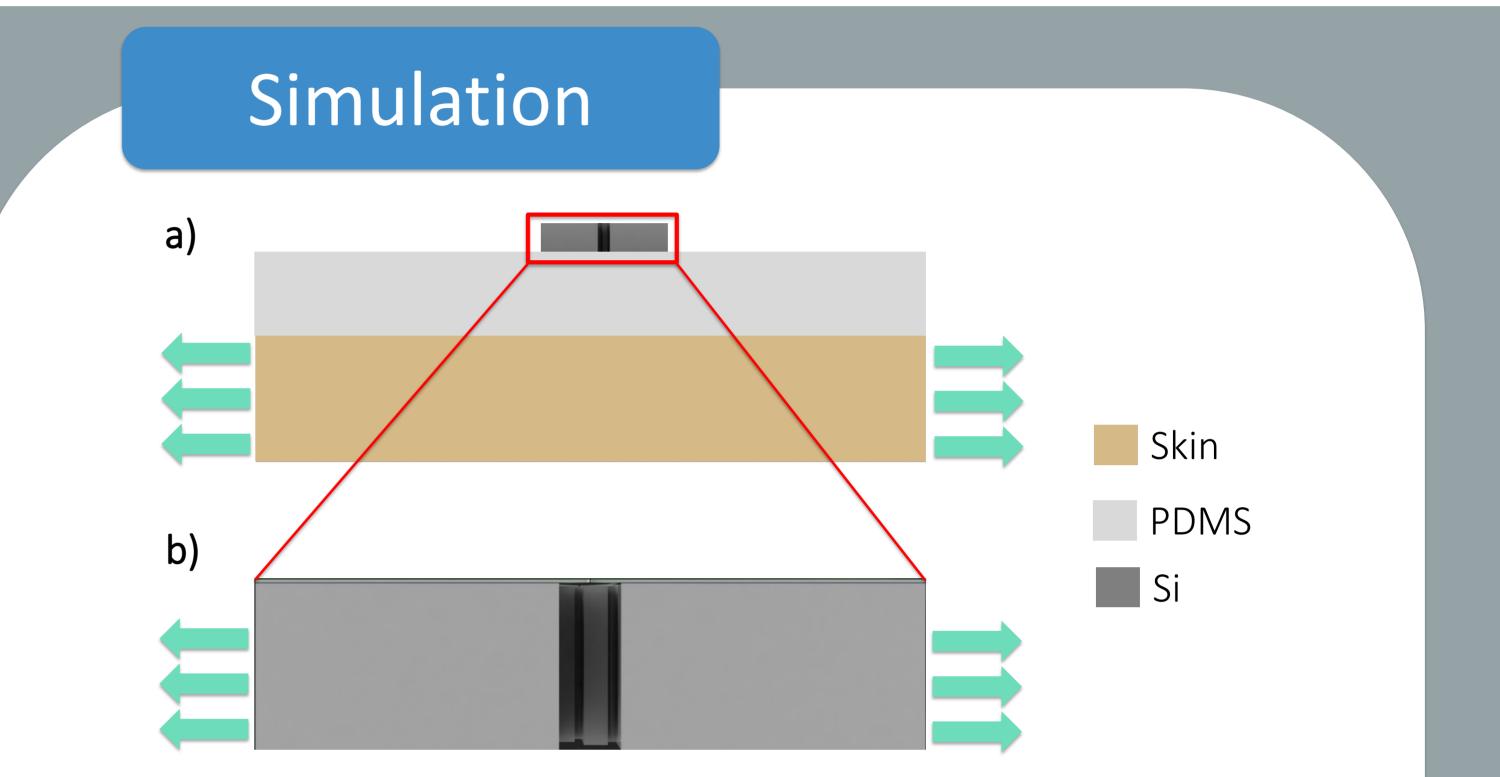
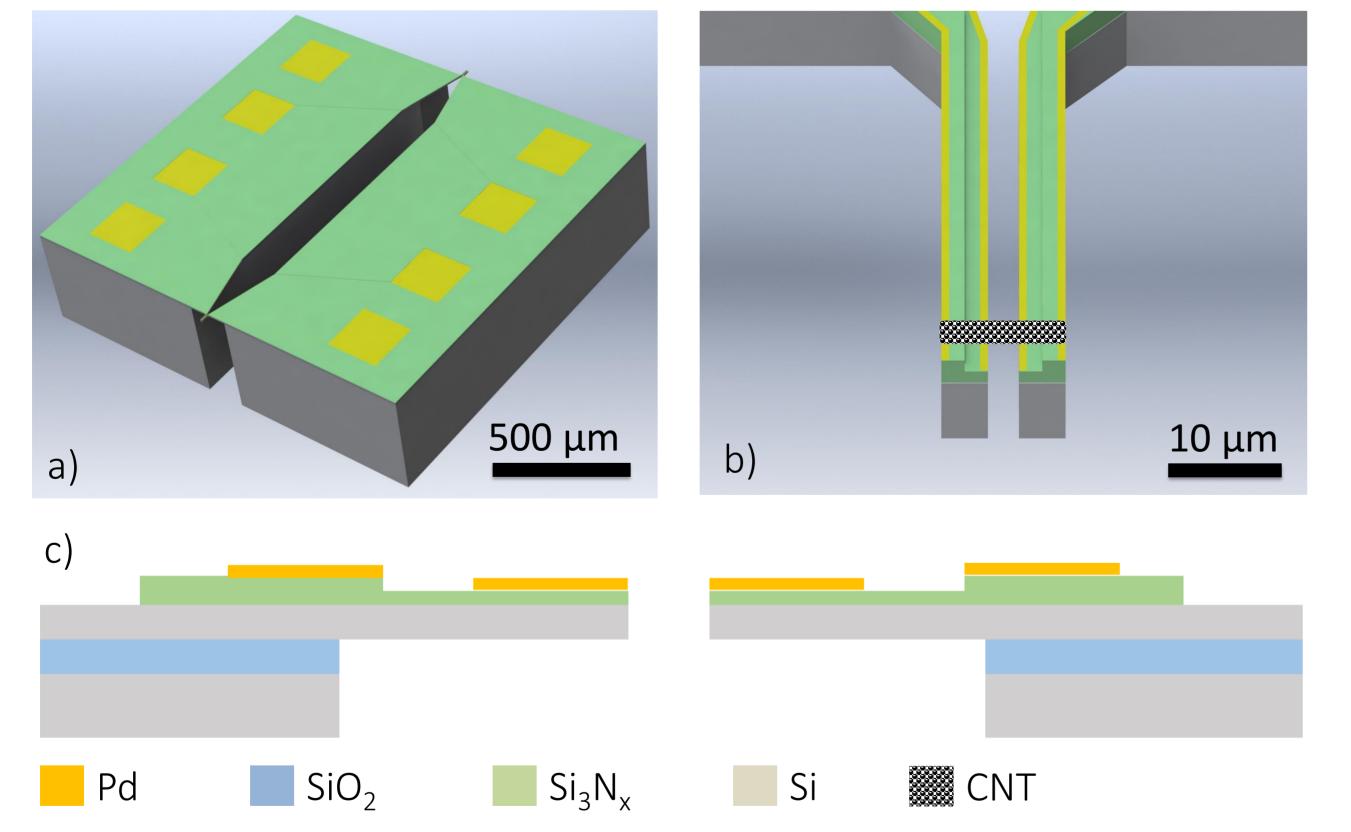


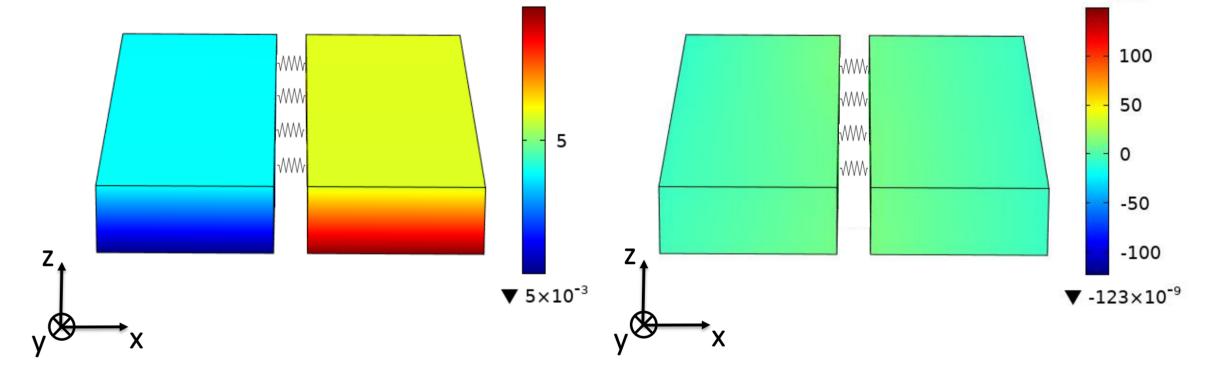
Figure 2 a) Model with Si device attached to PDMS on skin; b) Magnification of Si device with strain direction

Design & Concept

- Defined preferred direction to measure uniaxial strain with help of springs
- Suppress unwanted movements to ensure low mechanical cross-sensitivity



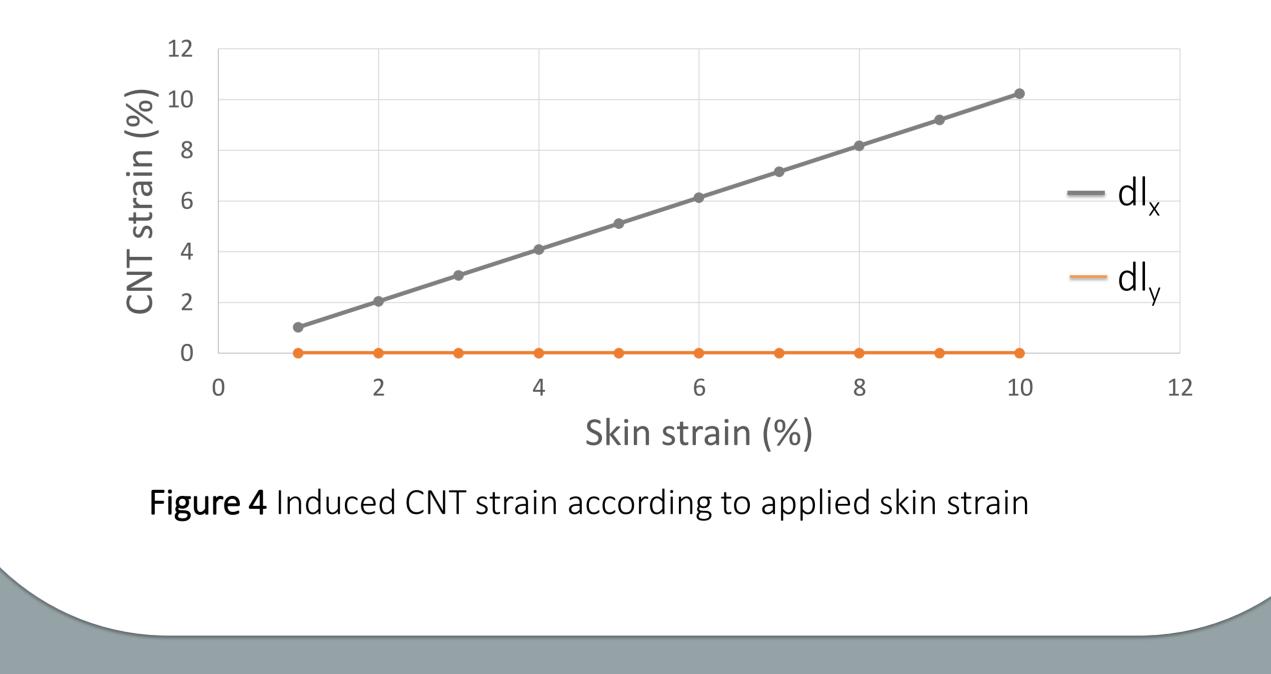




▲ 5×10⁻³

×10⁻³

Figure 3 Displacement of the silicon base a) in x-direction and b) in y-direction induced by skin strain



- Figure 1 a) CNT strain sensor device (spring design not shown); b) finger-like electrodes; c) scheme cross-sectional view
- Displacement between electrodes induce strain in suspended CNT
- Structuring according to bulk-micromachining
- Transfer of Si device with suspended CNT onto PDMS to transduce skin-strain into CNT

Conclusion

- Design heavily suppress displacement in y direction
- According to the current simulation model the skin strain is effectively transduce into CNT strain
- CNT strain effectively controllable with spring geometry and orientation



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▲ 149×10⁻⁹